



ZTX958

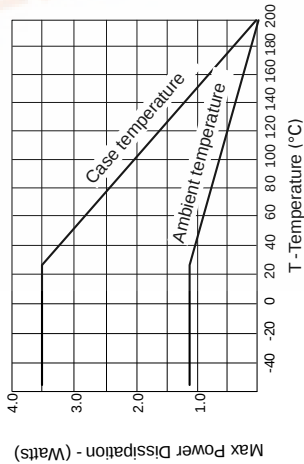
ELECTRICAL CHARACTERISTICS (at T_{amb} = 25°C)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Base-Emitter Turn-On Voltage	V _{BE(on)}		-690	-800	mV	I _C =500mA, V _{CE} =10V*
Static Forward Current Transfer Ratio	h _{FE}	100	200	300		I _C =10mA, V _{CE} =10V*
		100	200			I _C =500mA, V _{CE} =10V*
		10	20			I _C =1A, V _{CE} =10V*
Transition Frequency	f _T		85		MHz	I _C =100mA, V _{CE} =10V f=50MHz
Output Capacitance	C _{obo}		19		pF	V _{CE} =20V, f=1MHz
Switching Times	t _{on}		104		ns	I _C =500mA, I _B I=50mA
	t _{off}		2400		ns	I _B I=50mA, V _{CE} =100V

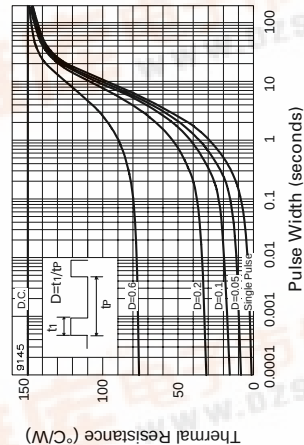
Measured under pulsed conditions. Pulse width=300μs. Duty cycle ≤2%

HERMAL CHARACTERISTICS

PARAMETER	SYMBOL	MAX.	UNIT
Thermal Resistance: Junction to Ambient Junction to Case	R _{th(j-amb)}	150	°CW
	R _{th(j-case)}	50	°CW



Derating curve



Maximum transient thermal impedance

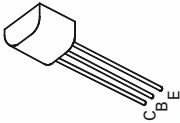
PNP SILICON PLANAR MEDIUM POWER
HIGH CURRENT TRANSISTOR

ISSUE 3 - JUNE 94

FEATURES

- * 0.5 Amp continuous current
- * Up to 1.5 Amps peak current
- * Very low saturation voltage
- * Excellent gain characteristics up to 1 Amp
- * Spice model available

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E-Line
TO92 Compatible

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V _{CBO}	-400	V
Collector-Emitter Voltage	V _{CEO}	-400	V
Emitter-Base Voltage	V _{EBO}	-6	V
Peak Pulse Current	I _{CM}	-1.5	A
Continuous Collector Current	I _C	-0.5	A
Practical Power Dissipation*	P _{totp}	1.58	W
Power Dissipation at T _{amb} =25°C	P _{tot}	1.2	W
Operating and Storage Temperature Range	T _J , T _{stg}	-55 to +200	°C

*The power which can be dissipated assuming the device is mounted in a typical manner on a P.C.B. with copper equal to 1 inch square minimum

ELECTRICAL CHARACTERISTICS (at T_{amb} = 25°C unless otherwise stated)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	V _{IBRCBO}	-400	-600		V	I _C =100μA
Collector-Emitter Breakdown Voltage	V _{IBRCER}	-400	-600		V	I _C =1μA, R _B ≤1KΩ
Collector-Emitter Breakdown Voltage	V _{IBRCEO}	-400	-550		V	I _C =10mA*
Emitter-Base Breakdown Voltage	V _{IBREBO}	-6	-8		V	I _E =100μA
Collector Cut-Off Current	I _{CBO}			-50 -1	nA μA	V _{CB} =300V V _{CE} =300V, T _{amb} =100°C
Collector Cut-Off Current	I _{CER} R ≤1KΩ			-50 -1	nA μA	V _{CB} =300V V _{CE} =300V, T _{amb} =100°C
Emitter Cut-Off Current	I _{EBO}			-10	nA	V _{EB} =6V
Collector-Emitter Saturation Voltage	V _{CE(sat)}		-100 -150 -300		mV mV mV	I _C =10mA, I _B =1mA*
						I _C =100mA, I _B =10mA*
						I _C =500mA, I _B =100mA*
Base-Emitter Saturation Voltage	V _{BE(sat)}		-790	-900	mV	I _C =500mA, I _B =100mA*

查询ZTX958供应商

捷多邦，专业PCB打样工厂，24小时加急出货

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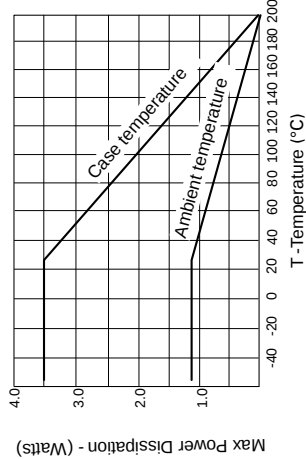
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Base-Emitter Turn-On Voltage	V _{BE(on)}		-690	-800	mV	I _C =-500mA, V _{CE} =-10V*
Static Forward Current Transfer Ratio	h _{FE}	100 100 10	200 200 20	300		I _C =-10mA, V _{CE} =-10V* I _C =-500mA, V _{CE} =-10V* I _C =-1A, V _{CE} =-10V*
Transition Frequency	f _T		85		MHz	I _C =-100mA, V _{CE} =-10V f=50MHz
Output Capacitance	C _{obo}		19		pF	V _{CE} =-20V, f=1MHz
Switching Times	t _{on} t _{off}		104 2400		ns ns	I _C =-500mA, I _B I=-50mA I _B I=50mA, V _{CC} =-100V

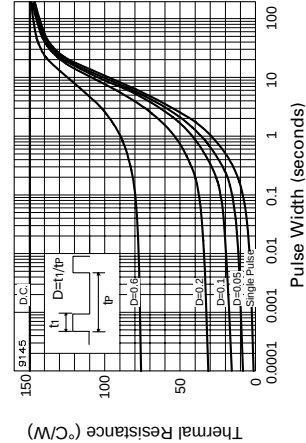
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Thermal Resistance: Junction to Ambient Junction to Case	R _{th(j-amb)} R _{th(j-case)}	150 50	°CW °CW



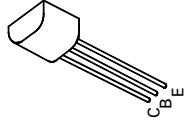
Derating curve



Maximum transient thermal impedance

FEATURES

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Collector-Emitter Breakdown Voltage	V _{IBRCEO}	-400	-550		V	I _C =-10mA*
Emitter-Base Breakdown Voltage	V _{IBREBO}	-6	-8		V	I _E =-100µA
Collector Cut-Off Current	I _{CBO}			-50 -1	nA µA	V _{CB} =-300V V _{CE} =-300V, T _{amb} =100°C
Collector Cut-Off Current	I _{CER} R ≤1KΩ			-50 -1	nA µA	V _{CB} =-300V V _{CE} =-300V, T _{amb} =100°C
Emitter Cut-Off Current	I _{EBO}			-10	nA	V _{EB} =-6V
Collector-Emitter Saturation Voltage	V _{CE(sat)}		-100 -150 -300	-150 -200 -400	mV mV mV	I _C =-10mA, I _B =-1mA* I _C =-100mA, I _B =-10mA* I _C =-500mA, I _B =-100mA*
Base-Emitter Saturation Voltage	V _{BE(sat)}		-790	-900	mV	I _C =-500mA, I _B =-100mA*

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TYPICAL CHARACTERISTICS

